

DATASHEET

Module TYPE	DDR3 8GB/4GB/2GB/1GB SODIMM
Module speed	PC3-12800
CAS Latency	CL-11
Pin	204pin
SDRAM Operating Temp	-40 °C ~ 85 °C

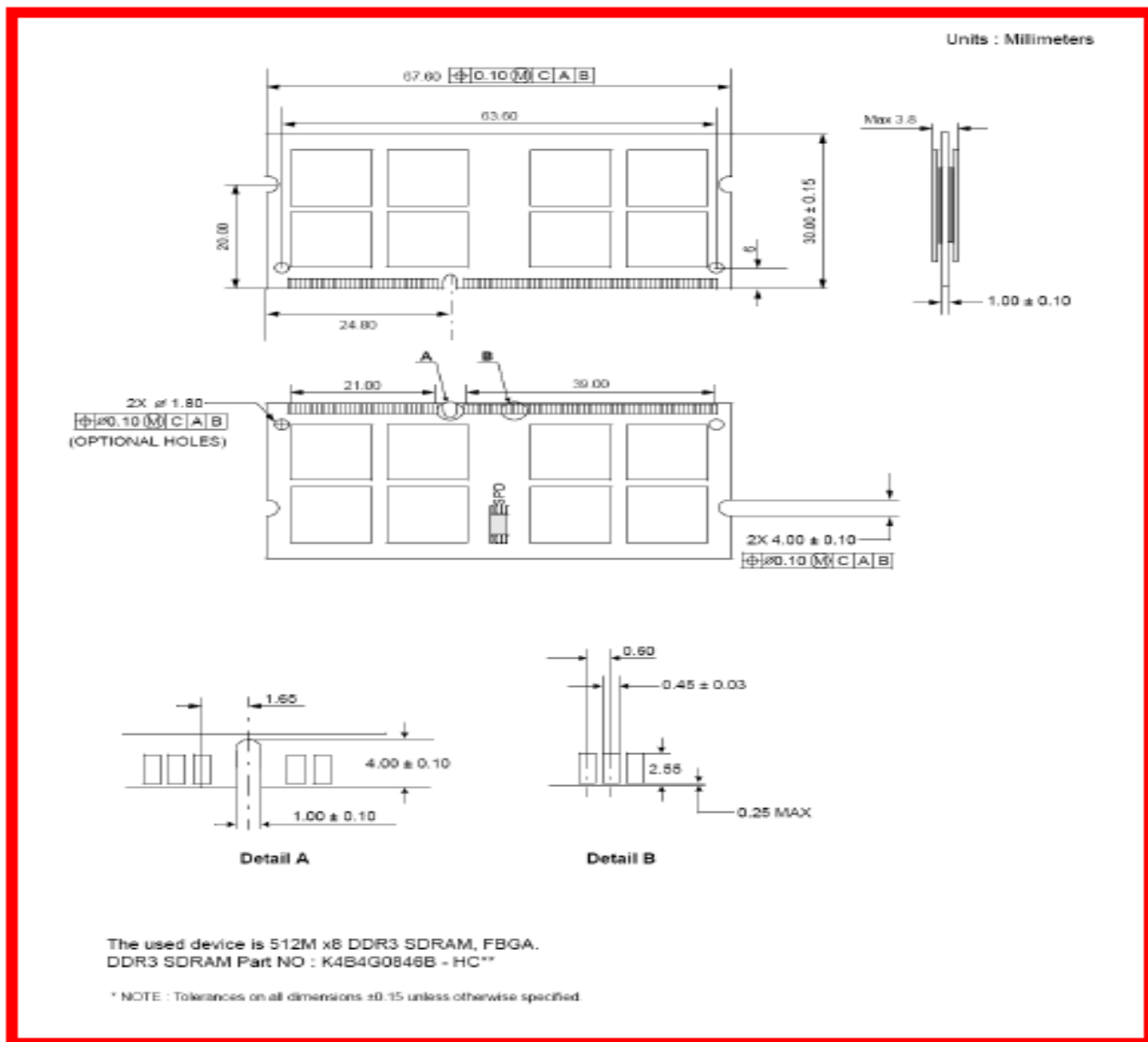
1. Features

Key Parameter

Industry Nomenclature	Speed Grade	Data Rate MT/s			tRCD	tRP	tRC
		CL=7	CL=9	CL=11	(ns)	(ns)	(ns)
PC3-12800	-	1066	1333	1600	13.125	13.125	13.125

- JEDEC Standard 204-pin Dual In-Line Memory Module
- Intend for PC3-12800 applications
- Inputs and Outputs are SSTL-15 compatible
- VDD=VDDQ= 1.5 Volt \pm 0.075
- VDD=VDDQ= 1.35 Volt (-0.067/+0.1V)
- Bi-directional Differential Data Strobe
- DLL aligns DQ and DQS transition with CK transition
- SDRAMs have 8 internal banks for concurrent operation
- Normal and Dynamic On-Die Termination support.
- SDRAMs are 78-ball BGA Package
- 8 bit pre-fetch
- Two different termination values (Rtt_Nom & Rtt_WR)
- Auto & self refresh 7.8 μ s ($T_A \leq +85^\circ\text{C}$)
- 30 μ "Golden Contactor
- DRAM operating temperature range
 - Industrial($-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$)
- Programmable Device Operation:
 - Burst Type: Sequential or Interleave
 - Device CAS# Latency: 9
 - Burst Length: switch on-the-fly:
 - BL=8 or BC 4
- RoHS Compliant (*Section 14*)

2. PACKAGE DIMENSION



Note: Device position is only for reference.

3. Ordering Information

Type & Speed	Density	Height	Innodisk Memory P/N
DDR3L-1600 SODIMM	8GB	1.18"	M3S0-8GMSDDPC
	4GB	1.18"	M3S0-4GMSCDPC
	2GB	1.18"	M3S0-2GMJCDPC
	1GB	1.18"	M3S0-1GMFCDPC